



# FGAF40N60UF

## 600 V PT IGBT

### General Description

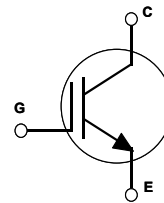
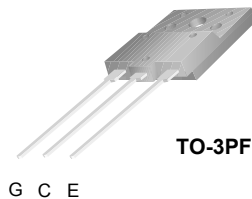
Fairchild®'s UF series of IGBTs provide low conduction and switching losses. The UF series is designed for applications such as general inverters and PFC where high speed switching is a required feature.

### Features

- High Speed Switching
- Low Saturation Voltage:  $V_{CE(sat)} = 2.3 \text{ V @ } I_C = 20 \text{ A}$
- High Input Impedance

### Applications

General Inverter, PFC



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	FGAF40N60UF	Unit
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current	@ $T_C = 25^\circ\text{C}$	40
		@ $T_C = 100^\circ\text{C}$	20
$I_{CM(1)}$	Pulsed Collector Current	160	A
$P_D$	Maximum Power Dissipation	@ $T_C = 25^\circ\text{C}$	100
		@ $T_C = 100^\circ\text{C}$	40
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	1.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\Delta BV_{CES}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	$\mu A$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA

### On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 20mA, V_{CE} = V_{GE}$	3.5	5.1	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 20A, V_{GE} = 15V$	--	2.3	3.0	V
		$I_C = 40A, V_{GE} = 15V$	--	3.1	--	V

### Dynamic Characteristics

$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	1075	--	pF
$C_{oes}$	Output Capacitance		--	170	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	50	--	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 20A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	15	--	ns
$t_r$	Rise Time		--	30	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	65	130	ns
$t_f$	Fall Time		--	35	100	ns
$E_{on}$	Turn-On Switching Loss		--	470	--	$\mu J$
$E_{off}$	Turn-Off Switching Loss		--	130	--	$\mu J$
$E_{ts}$	Total Switching Loss	--	600	1000	$\mu J$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 20A,$ $R_G = 10\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	30	--	ns
$t_r$	Rise Time		--	37	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	110	200	ns
$t_f$	Fall Time		--	80	250	ns
$E_{on}$	Turn-On Switching Loss		--	500	--	$\mu J$
$E_{off}$	Turn-Off Switching Loss		--	310	--	$\mu J$
$E_{ts}$	Total Switching Loss	--	810	1200	$\mu J$	
$Q_g$	Total Gate Charge	$V_{CE} = 300V, I_C = 20A,$ $V_{GE} = 15V$	--	77	150	nC
$Q_{ge}$	Gate-Emitter Charge		--	20	30	nC
$Q_{gc}$	Gate-Collector Charge		--	25	40	nC
$L_e$	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

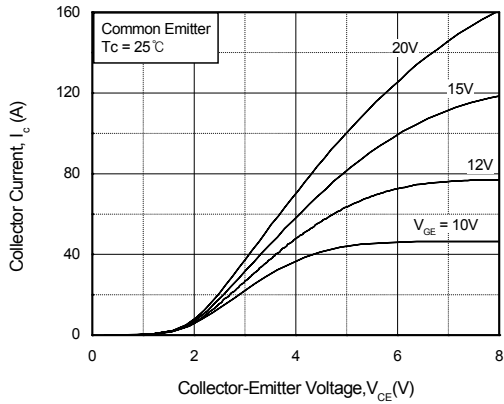


Fig 1. Typical Output Characteristics

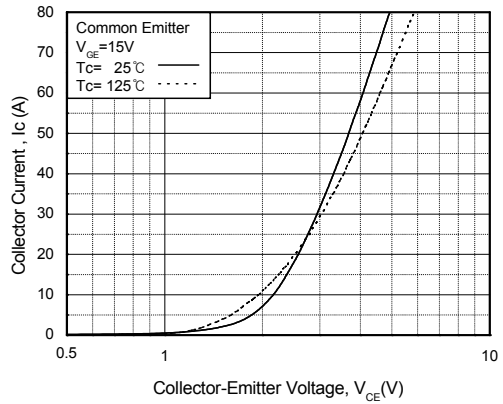


Fig 2. Typical Saturation Voltage Characteristics

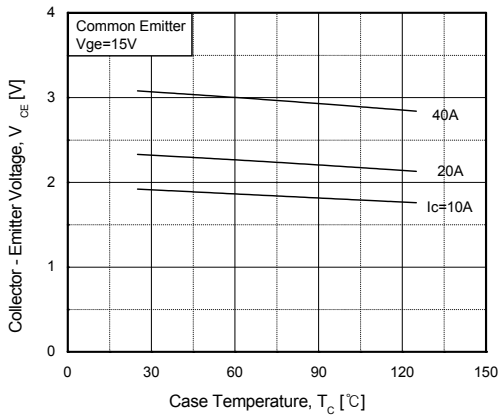


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

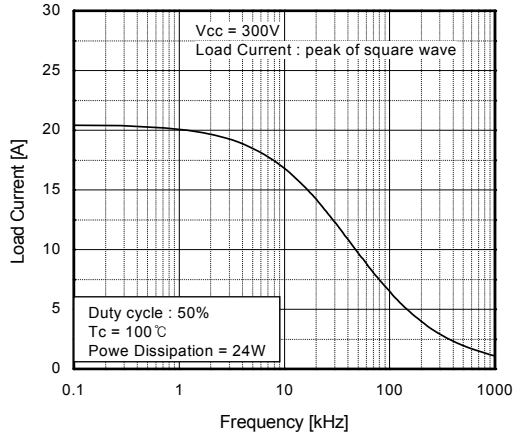


Fig 4. Load Current vs. Frequency

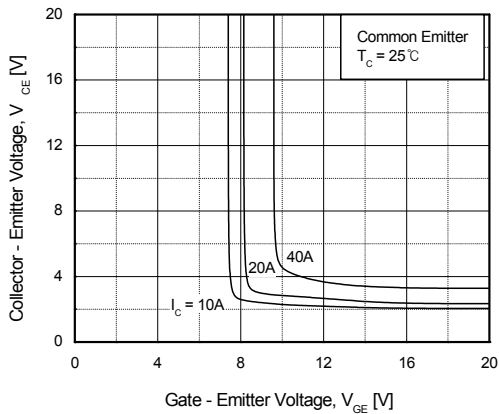


Fig 5. Saturation Voltage vs.  $V_{GE}$

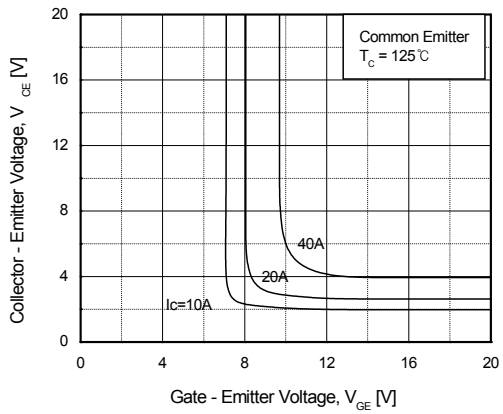


Fig 6. Saturation Voltage vs.  $V_{GE}$

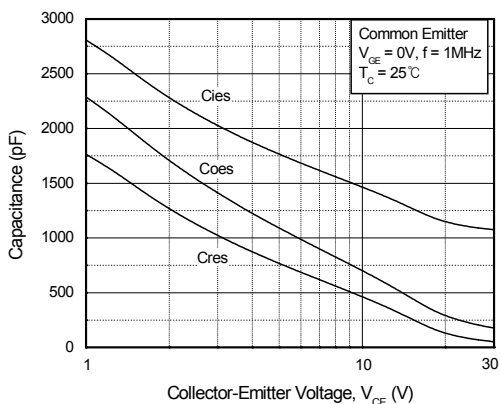


Fig 7. Capacitance Characteristics

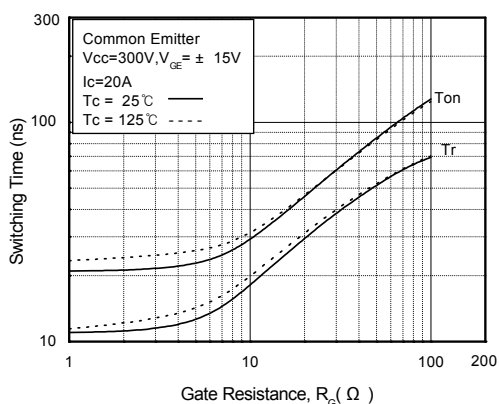


Fig 8. Turn-On Characteristics vs. Gate Resistance

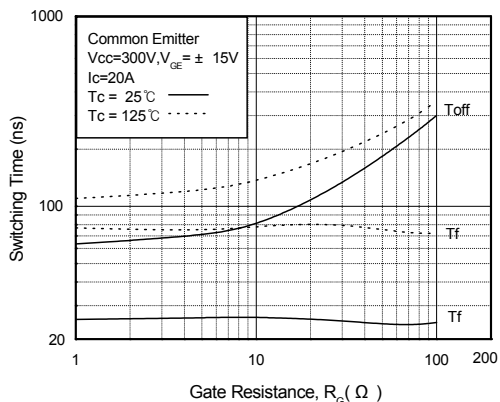


Fig 9. Turn-Off Characteristics vs. Gate Resistance

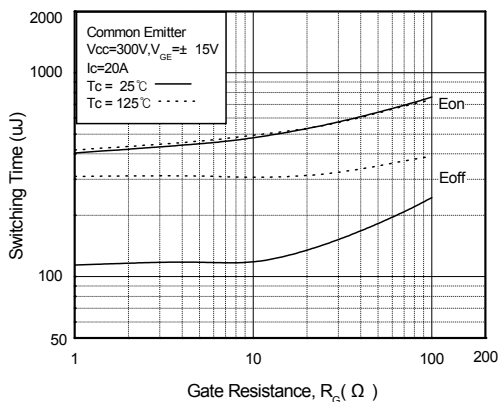


Fig 10. Switching Loss vs. Gate Resistance

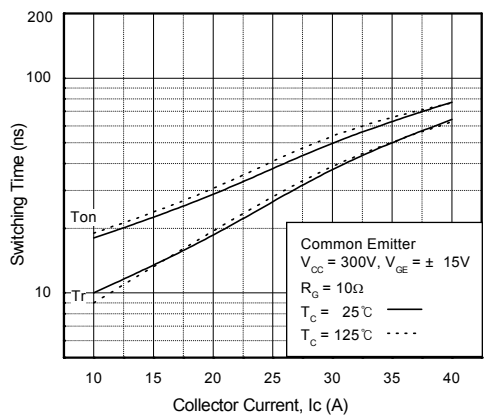


Fig 11. Turn-On Characteristics vs. Collector Current

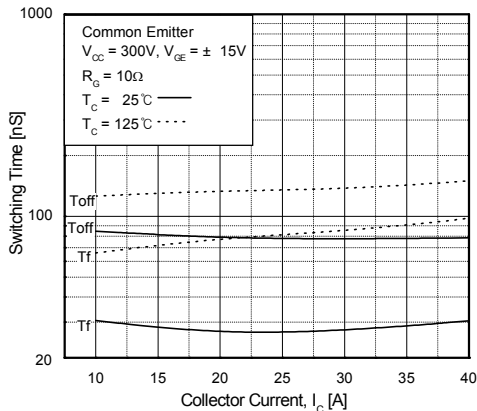


Fig 12. Turn-Off Characteristics vs. Collector Current

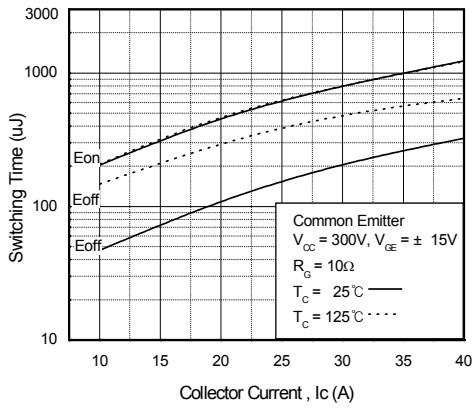


Fig 13. Switching Loss vs. Collector Current

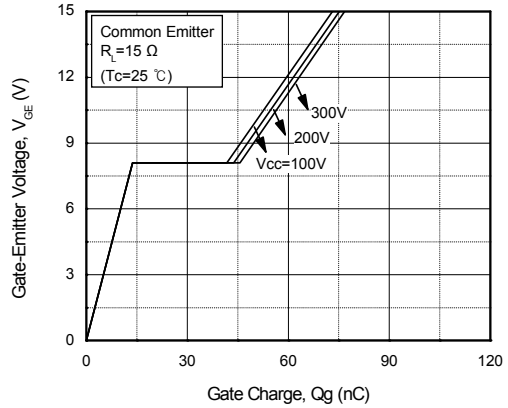


Fig 14. Gate Charge Characteristics

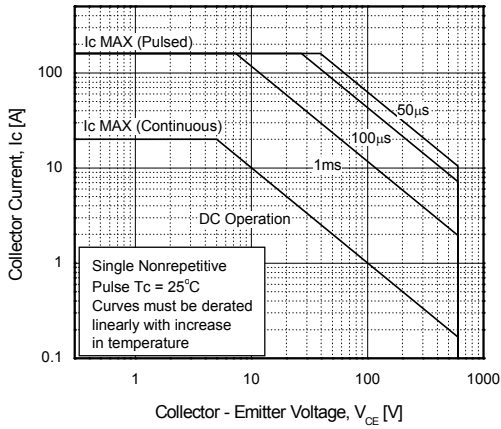


Fig 15. SOA Characteristics

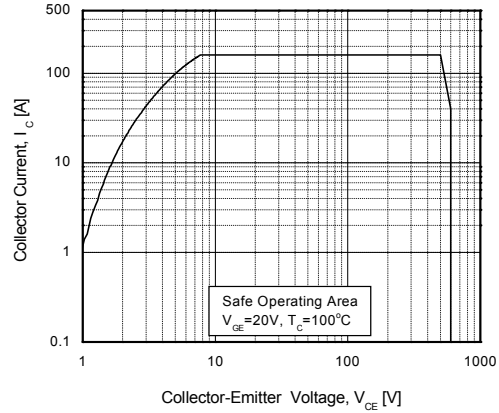


Fig 16. Turn-Off SOA Characteristics

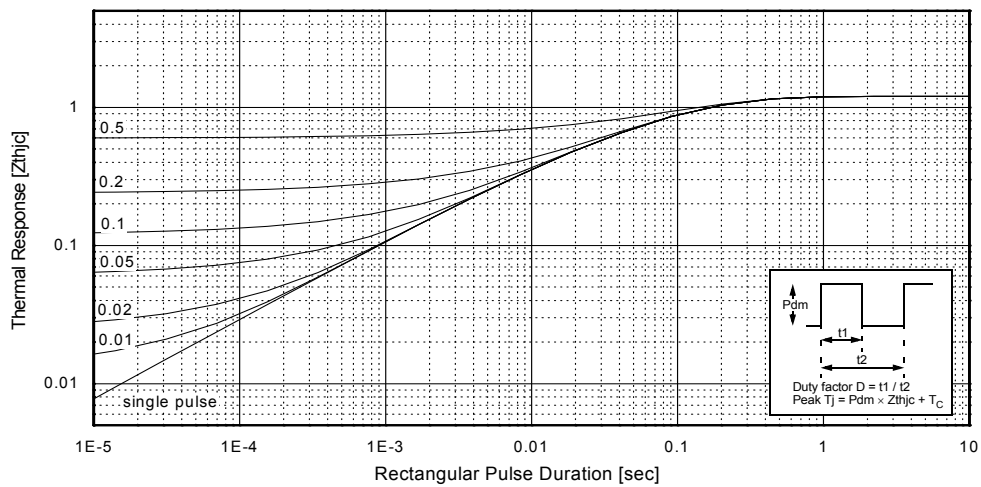
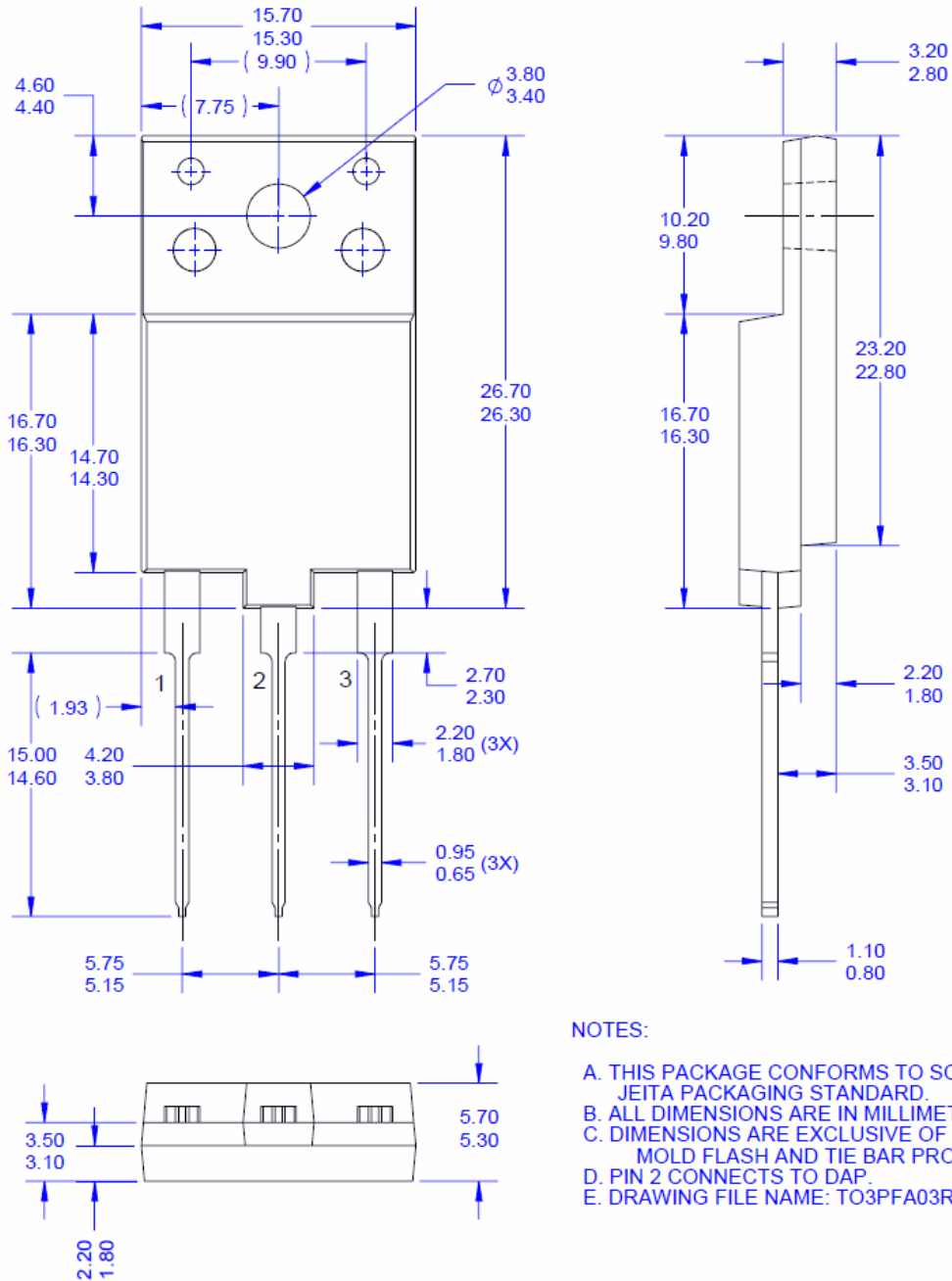


Fig 17. Transient Thermal Impedance of IGBT

Mechanical Dimensions

TO-3PF



NOTES:




- A. THIS PACKAGE CONFORMS TO SC94 JEITA PACKAGING STANDARD.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- D. PIN 2 CONNECTS TO DAP.
- E. DRAWING FILE NAME: TO3PFA03REV1

Dimensions in Millimeters



**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- |  |   |   |
|--|---|---|
| 2Cool™   | FPS™  | Sync-Lock™*   |
| AccuPower™   | F-PFST™   | SYSTEM GENERAL®*  |
| AX-CAP®*   | FRFET®  | TinyBoost™  |
| BiSiC™   | Global Power Resource™  | TinyBuck™   |
| Build it Now™  | Green Bridge™   | TinyCalc™   |
| CorePLUS™  | Green FPS™  | TinyLogic™  |
| CorePOWER™   | Green FPS™ e-Series™  | TINYOPTO™   |
| CROSSVOLT™   | Gmax™   | TinyPower™  |
| CTL™   | GTO™  | TinyPWM™  |
| Current Transfer Logic™  | IntelliMAX™   | TinyWire™   |
| DEUXPEED®  | ISOPLANAR™  | TranSiC®  |
| Dual Cool™   | Marking Small Speakers Sound Louder and Better™   | TriFault Detect™  |
| EcoSPARK®  | MegaBuck™   | TRUECURRENT®*   |
| EfficientMax™  | MICROCOUPLER™   | µSerDes™  |
| ESBC™  | MicroFET™   |  SerDes™ |
|  Fairchild® | MicroPak™   | UHC®  |
| Fairchild Semiconductor®   | MicroPak2™  | Ultra FRFET™  |
| FACT Quiet Series™   | MillerDrive™  | UniFET™   |
| FACT®  | MotionMax™  | VCX™  |
| FAST®  | mWSaver™  | VisualMax™  |
| FastvCore™   | OptoHiT™  | VoltagePlus™  |
| FETBench™  | OPTOLOGIC®  | XS™   |
|  | OPTOPLANAR®   |   |
|  | PowerTrench®  |   |
|  | PowerXS™  |   |
|  | Programmable Active Droop™  |   |
|  | QFET®   |   |
|  | QS™   |   |
|  | Quiet Series™   |   |
|  | RapidConfigure™   |   |
|  |  Saving our world, 1mW/W/kW at a time™ |   |
|  | SignalWise™   |   |
|  | SmartMax™   |   |
|  | SMART START™  |   |
|  | Solutions for Your Success™   |   |
|  | SPM®  |   |
|  | STEALTH™  |   |
|  | SuperFET®   |   |
|  | SuperSOT™-3   |   |
|  | SuperSOT™-6   |   |
|  | SuperSOT™-8   |   |
|  | SupreMOS®   |   |
|  | SyncFET™  |   |

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY A LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, [www.Fairchildsemi.com](http://www.Fairchildsemi.com), under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.



**Стандарт  
Электрон  
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

**Наши контакты:**

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331